

**29.** The method according to claim 27, wherein said respective first-conduction-type and second-conduction-type impurities are introduced at said third and fourth steps so that said introduction region for said first-conduction-type impurities and said introduction region for said second-conduction-type impurities are in contact with each other,

said antioxidant film being formed at said fifth step such that a contact portion of said respective introduction regions is exposed from said aperture.

**30.** The method according to claim 27, wherein said respective first-conduction-type and second-conduction-type impurities are introduced at said third and fourth steps so that a region is formed, neither said first-conduction-type impurities nor said second-conduction-type impurities being introduced into said region,

said antioxidant film being formed at said fifth step such that said region is exposed from said aperture, neither

said first-conduction-type impurities nor said second-conduction-type impurities having been introduced into said region.

**31.** The method according to claim 27, wherein

said respective first-conduction-type and second-conduction-type impurities are introduced at said third and fourth steps so that a region is formed, both said first-conduction-type impurities and said second-conduction-type impurities being introduced into said region,

said antioxidant film being formed at said fifth step such that said region is exposed from said aperture, both said first-conduction-type impurities and said second-conduction-type impurities having been introduced into said region.

**32.** The method according to claim 27, wherein

said antioxidant film is a silicon nitride film.

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